



P-Channel NexFET™ Power MOSFET

FEATURES

- Ultralow Q_q and Q_{qd}
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 2-mm × 2-mm Plastic Package

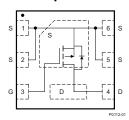
APPLICATIONS

- Battery Management
- Load Management
- Battery Protection

DESCRIPTION

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile. Low on resistance coupled with the extremely small footprint and low profile make the device ideal for battery operated space constrained applications.

Top View



R_{DS(on)} vs V_{GS} 150 $I_D = -3A$ R_{DS(on)} – On-State Resistance – mΩ 125 100 T_C = 125°C 75 50 25 $T_C = 25^{\circ}C$ 0 2 5 -V_{GS} - Gate to Source Voltage - V G006

PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage -20			V
Q_g	Gate Charge Total (–4.5V) 2.6			nC
Q_{gd}	Gate Charge Gate to Drain	0.5		nC
		$V_{GS} = -1.8V$	71	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = -2.5V 56		mΩ
		V _{GS} = -4.5V 39		mΩ
V _{GS(th)}	Threshold Voltage	-0.65		V

ORDERING INFORMATION

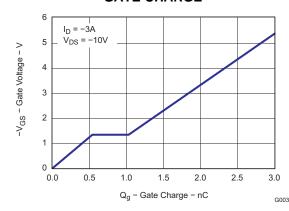
Device	Package	Media	Qty	Ship
CSD25302Q2	SON 2-mm x 2-mm Plastic Package	13-Inch Reel	3000	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 25$	°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage		V
V_{GS}	Gate to Source Voltage	±8	V
	Continuous Drain Current, T _C = 25°C	- 5	Α
I _D	Continuous Drain Current ⁽¹⁾	- 5	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	-20	Α
P _D	Power Dissipation	2.4	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	–55 to 150	ပိ

- (1) Package Limited
- (2) Pulse duration 10 µs, duty cycle ≤2%

GATE CHARGE





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



ELECTRICAL CHARACTERISTICS

 $T_{\rm v} = 25^{\circ} C_{\rm v}$ unless otherwise specified

Γ _A = 25°C, unless otherwise specified							
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Static CI	haracteristics						
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V$, $I_{DS} = -250\mu A$	-20			V	
I _{DSS}	Drain to Source Leakage	$V_{GS} = 0V, V_{DS} = -16V$			-1	μΑ	
I _{GSS}	Gate to Source Leakage	$V_{DS} = 0V$, $V_{GS} = \pm 8V$			-100	nA	
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = -250 \mu A$	-0.5	-0.65	-0.9	V	
		$V_{GS} = -1.8V$, $I_{DS} = -3.0A$		71	92	mΩ	
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = -2.5V$, $I_{DS} = -3.0A$		56	70	mΩ	
		$V_{GS} = -4.5V$, $I_{DS} = -3.0A$		39	49	$m\Omega$	
g _{fs}	Transconductance	$V_{DS} = -10V$, $I_{DS} = -3.0A$		12.3		S	
Dynamic	Characteristics						
C _{ISS}	Input Capacitance			270	350	pF	
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$		120	150	pF	
C _{RSS}	Reverse Transfer Capacitance			40	55	pF	
Qg	Gate Charge Total (-4.5V)			2.6	3.4	nC	
Q_{gd}	Gate Charge – Gate to Drain	$V_{DS} = -10V$, $I_{DS} = -3.0A$		0.5		nC	
Q_{gs}	Gate Charge Gate to Source			0.54		nC	
Qg(th)	Gate Charge at Vth			0.2		nC	
Q _{OSS}	Output Charge	$V_{DS} = -13V, V_{GS} = 0V$		2.3		nC	
t _{d(on)}	Turn On Delay Time			3.2		ns	
t _r	Rise Time	V 40V V 45V L 20A D 20		13.2		ns	
t _{d(off)}	Turn Off Delay Time	$V_{DS} = -10V$, $V_{GS} = -4.5V$, $I_{DS} = -3.0A$, $R_G = 2\Omega$		8.6		ns	
t _f	Fall Time			1.3		ns	
Diode C	haracteristics				•		
V _{SD}	Diode Forward Voltage	$I_{DS} = -3.0A, V_{GS} = 0V$		-0.8	-1.0	V	
Q _{rr}	Reverse Recovery Charge	V 42V I 200 4:/4t 2000 / -		2.5		nC	
t _{rr}	Reverse Recovery Time	$V_{dd} = -13V$, $I_F = -3.0A$, $di/dt = 300A/\mu s$		8.8		ns	
			•				

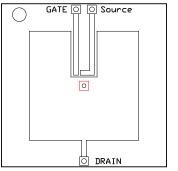
THERMAL CHARACTERISTICS

 $T_{\Delta} = 25^{\circ}C$, unless otherwise specified

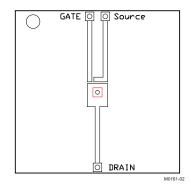
1A - 20	TA = 20 °C, amount will opening						
	PARAMETER	MIN	TYP	MAX	UNIT		
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾			8.6	°C/W		
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾			66	°C/W		

 ⁽¹⁾ R_{θJC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.





Max $R_{\theta JA} = 66^{\circ}\text{C/W}$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 207^{\circ} C/W$ when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $T_A = 25$ °C, unless otherwise specified

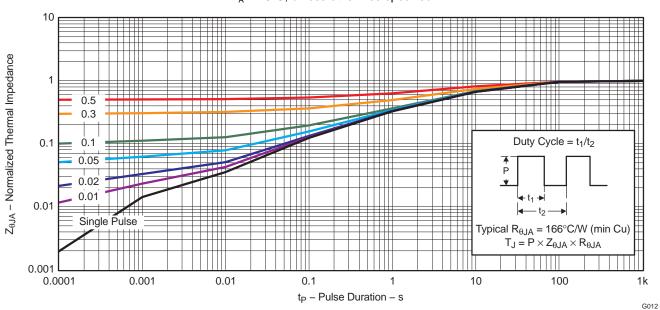


Figure 1. Transient Thermal Impedance



TYPICAL MOSFET CHARACTERISTICS (continued)

T_A = 25°C, unless otherwise specified

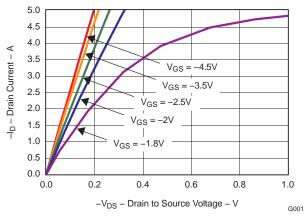


Figure 2. Saturation Characteristics

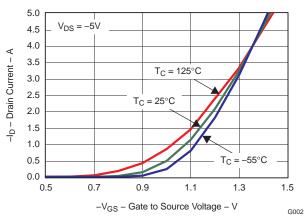


Figure 3. Transfer Characteristics

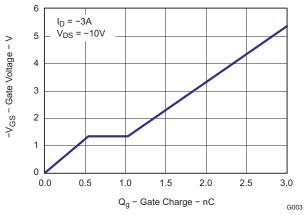


Figure 4. Gate Charge

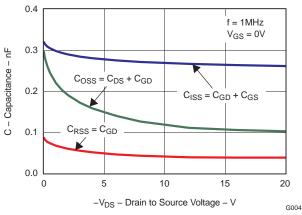


Figure 5. Capacitance

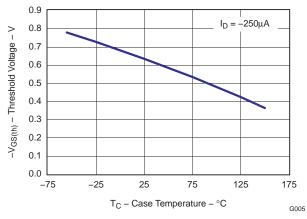


Figure 6. Threshold Voltage vs. Temperature

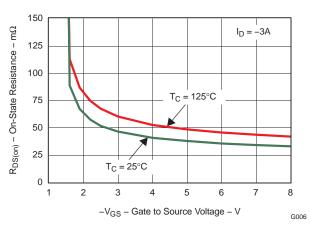


Figure 7. On-State Resistance vs. Gate to Source Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

$T_A = 25$ °C, unless otherwise specified

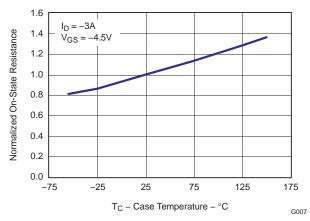


Figure 8. Normalized On-State Resistance vs. Temperature

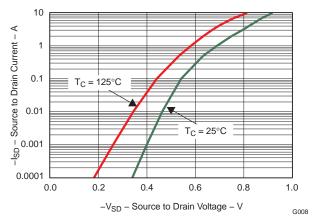


Figure 9. Typical Diode Forward Voltage

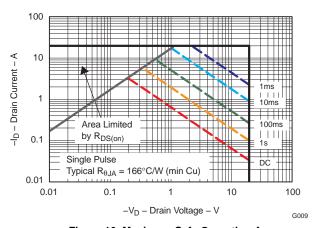


Figure 10. Maximum Safe Operating Area

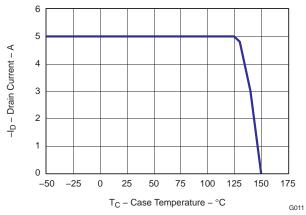
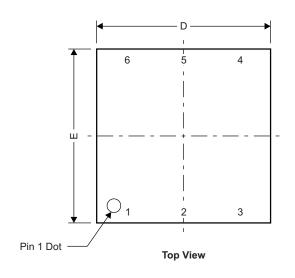


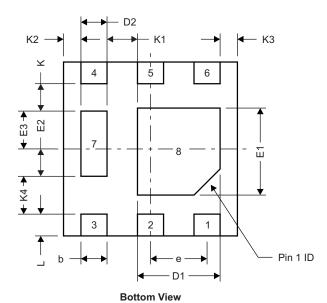
Figure 11. Maximum Drain Current vs. Temperature

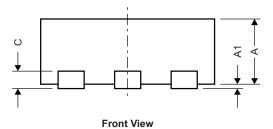


MECHANICAL DATA

Q2 Package Dimensions







Pinout

Source 1, 2, 5, 6, 8

Gate 3

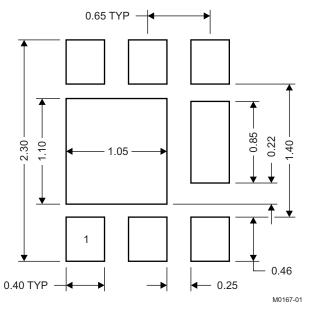
Drain 4, 7

M0175-01

MILLIMETERS				INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.700	0.750	0.800	0.028	0.030	0.032	
A1	0.000		0.050	0.000		0.002	
b	0.250	0.300	0.350	0.010	0.012	0.014	
С		0.203 TYP			0.008 TYP		
D		2.000 TYP			0.080 TYP		
D1	0.900	0.950	1.000	0.036	0.038	0.040	
D2		0.300 TYP		0.012 TYP			
Е		2.000 TYP			0.080 TYP		
E1	0.900	1.000	1.100	0.036 0.040 0.044			
E2		0.280 TYP		0.0112 TYP			
E3		0.470 TYP		0.0188 TYP			
е		0.650 BSC			0.026 TYP		
K		0.280 TYP			0.0112 TYP		
K1		0.350 TYP		0.014 TYP			
K2		0.200 TYP			0.008 TYP		
K3		0.200 TYP			0.008 TYP		
K4		0.470 TYP		0.0188 TYP			
L	0.200	0.25	0.300	0.008	0.010	0.0121	



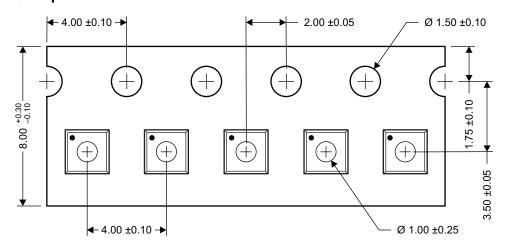
Recommended PCB Pattern

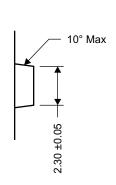


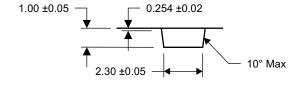
Note: All dimensions are in mm, unless otherwise specified.

For recommended circuit layout for PCB designs, see application note SLPA005 - Reducing Ringing through PCB Layout Techniques.

Q2 Tape and Reel Information







M0168-01

Notes: 1. Measured from centerline of sprocket hole to centerline of pocket

- 2. Cumulative tolerance of 10 sprocket holes is ±0.20
- 3. Other material available
- 4. Typical SR of form tape Max 108 OHM/SQ
- 5. All dimensions are in mm, unless otherwise specified.



REVISION HISTORY

Changes from Original (November 2009) to Revision A			
•	Deleted the Package Marking Information section		8

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